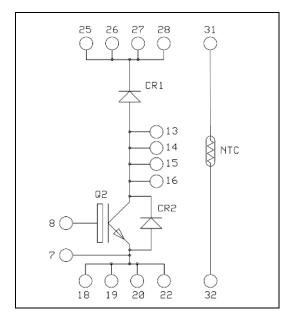
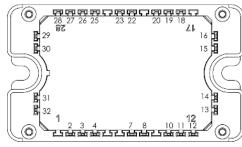


Boost chopper High speed IGBT 5 Power Module

# $V_{CES} = 650V$ $I_{C} = 200A$ @ Tc = 25°C





Pins 25/26/27/28 ; 13/14/15/16 ; 18/19/20/22 must be shorted together

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- High speed IGBT 5
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Low leakage current
- Very low stray inductance
- Internal thermistor for temperature monitoring

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant



#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	200	
I <sub>C</sub>	Continuous Conector Current	$T_C = 80^{\circ}C$	120	А
I <sub>CM</sub>	Pulsed Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	400	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
P <sub>D</sub>	Power Dissipation		483	W

💱 🚓 UTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



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# **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				200	μA
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.65	2.2	V
		$I_{\rm C} = 200 {\rm A}$	$T_{j} = 150^{\circ}C$		1.9		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$		3.3	4.0	4.7	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				480	nA

# **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$			12		
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 25V$			0.2		nF
Cres	Reverse Transfer Capacitance	f = 1MHz		0.044			
Q <sub>G</sub>	Gate charge	$V_{GE} = 15V, I_C = 200A$ $V_{CE} = 520V$			480		nC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch		21			
Tr	Rise Time	$V_{GE} = 15V$			15		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 400V$ $I_{C} = 100A$			180		
$T_{\rm f}$	Fall Time	$R_G = 1\Omega$			18		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Swite		20		ns	
Tr	Rise Time	$V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 100A$			15		
T <sub>d(off)</sub>	Turn-off Delay Time				205		
$T_{\rm f}$	Fall Time	$R_G = 1\Omega$			26		
Eon	Turn on Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$	$T_j = 150^{\circ}C$		3		mJ
E <sub>off</sub>	Turn off Energy	$I_{\rm C} = 100 {\rm A}$ $R_{\rm G} = 1 {\rm \Omega}$	$T_j = 150^{\circ}C$		1.2		1115
R <sub>Gint</sub>	Integrated gate resistor				1.25		Ω
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.31	°C/W

### Diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage					650	V
I <sub>RM</sub>	Reverse Leakage Current	$V_R = 650V$				200	μA
I <sub>F</sub>	DC Forward Current		$Tc = 25^{\circ}C$		200		А
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 200 {\rm A}$	$T_i = 25^{\circ}C$		1.6	2.2	v
		$V_{GE} = 0V$	$T_i = 150^{\circ}C$		1.65		v
t <sub>rr</sub>	Reverse Recovery Time	I = 100 A	$T_j = 25^{\circ}C$		46		ns
			$T_{j} = 150^{\circ}C$		62		115
0	Devenue Deservery Change	$v_R = 400 v$ di/dt =6000A/µs	$T_j = 25^{\circ}C$		2		
Q <sub>rr</sub>	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		4		μC
R <sub>thJC</sub>	Junction to Case Thermal Resistance				0.35	°C/W	



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### Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

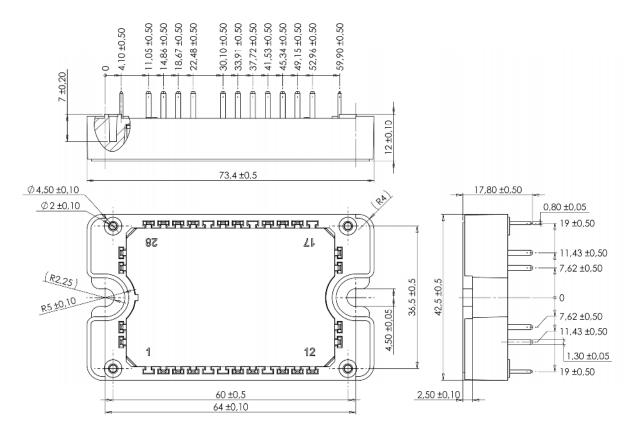
Symbol	Characteristic		,	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C				50		kΩ
$\Delta R_{25}/R_{25}$					5		%
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$				3952		Κ
$\Delta B/B$			T <sub>C</sub> =100°C		4		%
		D					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$  T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

### Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T <sub>J</sub>	Operating junction temperature range			-40	175	
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max -25	°C
T <sub>STG</sub>	Storage Temperature Range			-40	125	C
T <sub>C</sub>	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

# Package outline (dimensions in mm)



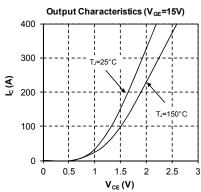
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

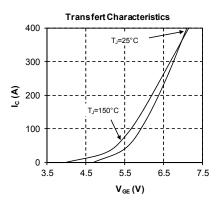
APTGTQ200DA65T3G-Rev 1 January, 2017



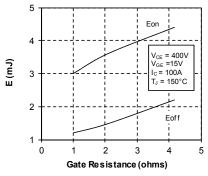
### Power Matters."

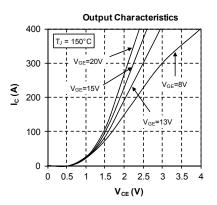
## Typical performance curve

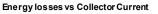


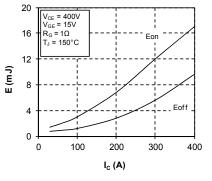


Switching EnergyLosses vs Gate Resistance

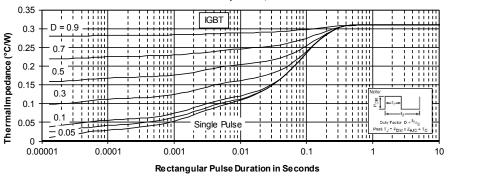








Maxim um Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



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4 - 6



0.1

0 0.00001 ....

0.0001

0.1

0.05

# APTGTQ200DA65T3G

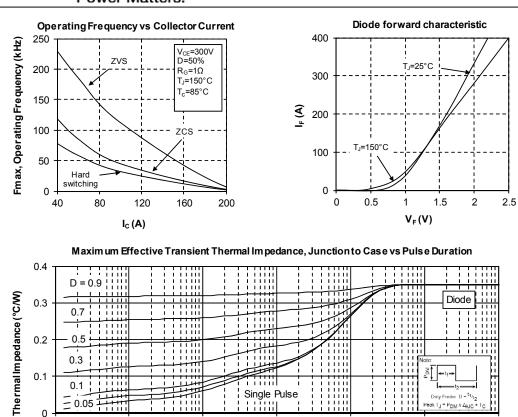
Post

1

 $\mathsf{D} = {}^{t_1} \wedge_2$ 

10

eak Tj = P<sub>DM</sub> × Z<sub>6JC</sub>



. . . . . . Single Pulse

0.01

**Rectangular Pulse Duration in Seconds** 

0.1

1111

0.001

APTGTQ200DA65T3G-Rev 1 January, 2017

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